

ABSTRACT

1 A data storage device that includes an array of resistive memory cells and a circuit
2 that is electrically connected to the array. The resistive memory cells include magnetic
3 random access memory cells that are electrically connected to diodes. The circuit is
4 capable of applying a first voltage to some of the resistive memory cells in the array, a
5 second voltage to other cells in the array, and a third voltage to yet other cells in the array.
6 Also, a method of sensing the resistance state of a selected resistive memory cell using
7 the circuit.